



AP22653Q

PRECISON-ADJUSTABLE CURRENT-LIMITED AUTOMOTIVE-COMPLIANT POWER SWITCH

Description

The automotive-compliant AP22653Q is a , single-channel, precision-adjustable, current-limited switch optimized for applications that require accurate current limiting, or to provide up to 1.5A of continuous load current during heavy loads/short circuits. This device offers an adjustable current-limit threshold between 125mA and 1735mA (typ) via an external resistor. Current limit accuracy of $\pm 7\%$ can be achieved at high current-limit settings. The rise and fall times are controlled to minimize current surges during turn on/off.

The device has fast short-circuit response time for improved overall system robustness. The device provides a complete protection solution for applications subject to heavy capacitive loads and the prospect of short circuit, offering reverse current blocking and limiting; overcurrent, overtemperature, and short-circuit protection; and controlled rise-time and undervoltage lockout functionality. A 6ms deglitch capability on the open-drain flag output prevents false overcurrent reporting and does not require any external components.

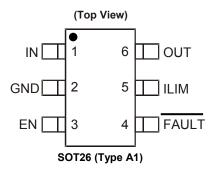
The AP22653Q limits the output current to a safe level when the output current exceeds current-limit threshold and folds back the output current when subjected to short-circuit conditions.

The device is available in the SOT26 (Type A1) package.

Applications

- Automotive ECU Supply Rail Power Distribution and Switching
- Automotive ECU Supply Rail Precision Current Limiting

Pin Assignments



Features

- AEC qualified to AEC-Q100 Grade 1 offering -40°C to 125°C
 Ambient Operating Temperature Range
- Up to 1.5A Maximum Load Current
- Accurate Adjustable Current Limit, 125mA to 1735mA
- ±7% Accurate Adjustable Current Limit, 1.735A with R_{I IM} = 15kΩ
- Constant-Current Version
- Fast Short-Circuit Response Time: 5µs (Typ.)
- Reverse Current Blocking During Shutdown and Reverse Current Limiting During Enable
- Operating Range: 3.0V to 5.5V
- Built-In Soft-Start with 0.5ms Typical Rise Time
- Overcurrent, Output Overvoltage, and Thermal Protection
- Fault Report (FAULT) with Blanking Time
- ESD Protection: 2kV HBM, 750V CDM
- Enable Active High
- SOT26 Package: Available in "Green" Molding Compound (No Br, Sb)
- 16kV ESD Protection per IEC61000-4-2 (With External Capacitance)
- UL Recognized.
- IEC60950-1 CB Scheme Certified
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The AP22653Q is suitable for automotive applications requiring specific change control; this part is AEC-Q100 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

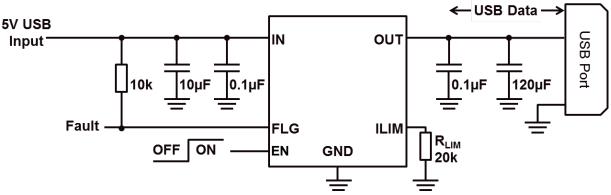
https://www.diodes.com/quality/product-definitions/

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Typical Applications Circuit (Note 4)



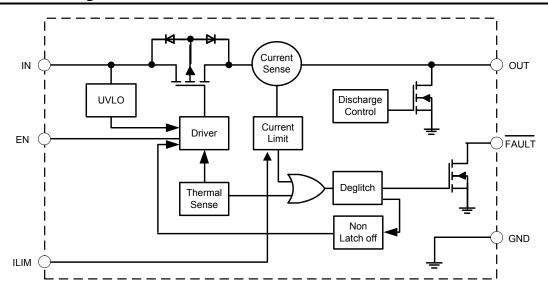
Note:

4. 120µF Output Capacitance is a Requirement of USB.

Pin Descriptions

Pin Name	Pin Number	I/O	Function	
IN	1	ı	Input, connect a 0.1μF or greater ceramic capacitor from IN to GND as close to IC as possible.	
GND	2	_	Ground, connect to external exposed pad.	
EN	3	I	Enable input, logic high turns on power switch.	
FAULT	4	0	Active-low open-drain output, asserted during overcurrent, overtemperature, or reverse-voltage conditions.	
ILIM	5	0	Use external resistor to set current-limit threshold; recommended $15k\Omega \le R_{LIM} \le 210k\Omega$	
OUT	6	0	Voltage Output Pin, connect a $0.1\mu F$ bypass capacitor and a high-value capacitor to GND, close to IC. (At least $10\mu F$ in USB application.)	
Exposed Pad	_	_	Internal connection to GND; Connect to GND externally for improved power dissipation. It should not be used as electrical ground conduction path.	

Functional Block Diagram





Absolute Maximum Ratings (@ TA = +25°C, unless otherwise specified.)

	Symbol	Parameter		Ratings	Unit		
	HBM	Human Body Model ESD Protection, per AEC Q10	2	kV			
ESD	CDM Charged Device Model ESD Protection, per AEC Q100-011			750	V		
LOD	IEC System Level	Surges per IEC61000-4-2. 1999 Applied to Output Terminals of EVM (Note 6)	16	kV			
	V _{OUT} , V _{FAULT} , V _{ILIM} , V _{EN}	Voltage on IN, OUT, FAULT, ILIM, EN		-0.3 to +6.0	V		
	Continuous FAULT Sink Current			25	mA		
	_	ILIM Source Current		1	mA		
	I _{LOAD}	Maximum Continuous Load Current	m Continuous Load Current		Α		
	T _{J(MAX)}	Maximum Junction Temperature		Maximum Junction Temperature		-40 to +150	°C
	T _{STG}	Storage Temperature Range (Note 5)		Storage Temperature Range (Note 5)		-65 to +150	°C
	R _{⊝JA}	Thermal Resistance, Junction to Ambient (Note 8) SOT26		120	°C/W		
	R _{OJC}	Thermal Resistance, Junction to Case (Note 8) SOT26		35	°C/W		

Notes:

- 5. UL Recognized Rating from -30°C to +70°C (Diodes Incorporated qualified T_{STG} from -65°C to +150°C).
- 6. External capacitors need to be connected to the output, EVM board was tested with external capacitor. This level is a pass test only and not a limit.
- 7. AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.
- 8. The JEDEC high-K (2s2p) board used to derive this data was a 3inch x 3inch, multilayer board with 1oz internal power and ground planes with 2oz copper traces on top and bottom of the board.

Caution:

Stresses greater than the 'Absolute Maximum Ratings' specified above, can cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability can be affected by exposure to absolute maximum rating conditions for extended periods of time.

Semiconductor devices are ESD sensitive and can be damaged by exposure to ESD events. Suitable ESD precautions should be taken when handling and transporting these devices.

Recommended Operating Conditions (@ TA = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit
V _{IN}	Input Voltage	3	5.5	V
I	Continuous Output Current (-40°C ≤ T _J ≤ +105°C)	0	1.5	Α
Іоит	Continuous Output Current (-40°C ≤ T _J ≤ +125°C)	0	1.2	А
V _{EN}	Enable Voltage	0	5.5	V
V _{IH}	High-Level Input Voltage on EN	1.5	V _{IN}	V
V _{IL}	Low-Level Input Voltage on EN	0	0.4	V
R _{LIM}	Current-Limit Threshold Resistor Range (1% Initial Tolerance)	15	210	kΩ
lo	Continuous FAULT Sink Current	0	10	mA
_	Input De-Coupling Capacitance, IN to GND	0.1		μF
т.	Operating Junction Temperature Io∪⊤ ≤ 1.5 A	-40	+105	°C
TJ	Operating Junction Temperature Io∪⊤ ≤ 1.2 A	-40	+125	°C



$\textbf{Electrical Characteristics} \ (\textcircled{@} \ T_{A} = +25 ^{\circ}\text{C}, \ V_{IN} = 3.0 \text{V to } 5.5 \text{V}, \ V_{EN} = \underline{0 \text{V or } V_{EN} = V_{IN}, \ R_{FAULT} = 10 \text{k}\Omega, \ unless otherwise specified.})$

Symbol	Parameter	Test Conditions (Note 9)			Тур	Max	Unit
Supply	•						
V _{UVLO}	Input UVLO	V _{IN} Rising	V _{IN} Rising		2.65	2.95	V
ΔV_{UVLO}	Input UVLO Hysteresis	V _{IN} Decreasing		_	65	_	mV
I _{SHDN}	Input Shutdown Current	V _{IN} = 5.5V, Disabled, OUT = C	pen	_	0.1	1	μΑ
	Input Quiggoont Current	V _{IN} = 5.5V, Enabled, OUT = O	pen, R _{LIM} = 20kΩ	_	140	160	μΑ
lQ	Input Quiescent Current	V _{IN} = 5.5V, Enabled, OUT = O	pen, R _{LIM} = 210kΩ	_	120	140	μΑ
I _{REV}	Reverse Leakage Current	Disabled, V _{IN} = 0V, V _{OUT} = 5.5	V, I _{REV} at V _{IN}	_	0.01	1	μΑ
Power Switch	ch			_			
R _{DS(ON)}	Switch On-Resistance	ISO 126 (Type A1) Package F	$T_A = +25^{\circ}C$, $V_{IN} = 5.0V$	_	55	90	mΩ
NDS(ON)	Owiter On-Resistance		-40°C ≤ T _A ≤ +125°C	_	_	135	11122
t _R	Output Turn-On Rise Time	$V_{IN} = 5.5V$, $C_L = 1\mu F$, $R_{LOAD} =$	100Ω. See Figure 1	_	0.5	1.5	ms
чR	Output rum-on ruse rime	$V_{IN} = 3.0V, C_L = 1\mu F, R_{LOAD} =$	100Ω.	_	0.3	1	ms
+_	Output Turn-Off Fall Time	$V_{IN} = 5.5V$, $C_L = 1\mu F$, $R_{LOAD} =$	100Ω. See Figure 1	_	0.25	0.5	ms
t _F	Output Turri-On Fail Time	$V_{IN} = 3.0V, C_L = 1\mu F, R_{LOAD} =$	100Ω.	_	0.28	0.5	ms
Current Lim	it						
	Current-Limit Threshold (Maximum DC Output Current),	R _{LIM} = 15kΩ	T _A = +25°C	1614	1735	1856	mA
			-40°C ≤ T _A ≤ +125°C	1536	1735	1933	
		$R_{LIM} = 20 \mathrm{k}\Omega$	T _A = +25°C	1196	1286	1376	
I _{LIMIT}			-40°C ≤ T _A ≤ +125°C	1132	1286	1440	
LIMIT	$V_{IN} = 5V$, $V_{OUT} = 4.5V$	$R_{LIM} = 49.9k\Omega$	T _A = +25°C	456	490	524	
		KLIM - 49.9K2	-40°C ≤ T _A ≤ +125°C	411	490	566	
		$R_{LIM} = 210k\Omega$	T _A = +25°C	95	125	155]
		R _{LIM} Shorted to GND		40	80	120	
		$R_{LIM} = 15k\Omega$, $T_A = +25^{\circ}C$		_	470		
		$R_{LIM} = 20k\Omega$, $T_A = +25^{\circ}C$		_	350	_	mA
I _{SHORT}	Short-Circuit Current Limit, OUT Connected to GND	$R_{LIM} = 49.9k\Omega$, $T_A = +25^{\circ}C$		_	140		
		$R_{LIM} = 210k\Omega, T_A = +25^{\circ}C$		_	35	_	
	R _{LIM} Shorted to GND, T _A = +25°C			80			
Enable Pin				_			
I _{LEAK-EN}	EN Input Leakage Current	V _{IN} = 5V, V _{EN} = 0V and 5.5V			_	2	μΑ
ton	Turn-On Time	$C_L = 1\mu F$, $R_L = 100\Omega$. See Figure 1			_	4	ms
toff	Turn-Off Time	C_L = 1 μ F, R_L = 100 Ω . See Figure 1			_	1	ms
Output Disc	harge						
R _{DIS}	Discharge Resistance (Note 10)	V _{IN} = 5V, Disabled, I _{OUT} = 1m/	4	<u> </u>	600	_	Ω

Notes: 9. Pul

^{9.} Pulse-testing techniques maintain junction temperature close to ambient temperature; thermal effects must be taken into account separately.

^{10.} The discharge function is active when the device is disabled (when enable is de-asserted or during power-up power-down when V_{IN} < V_{UVLO}). The discharge function offers a resistive discharge path for the external storage capacitor for limited time.



Electrical Characteristics (@ T_A = +25°C, V_{IN} = 3.0V to 5.5V, V_{EN} = 0V or V_{EN} = V_{IN} , R_{FAULT} = 10k Ω , unless otherwise specified.) (continued)

Symbol	Parameter	Test Conditions (Note 9)	Min	Тур	Max	Unit			
Reverse Vo	Reverse Voltage Protection								
V_{RVP}	Reverse-Voltage Comparator Trip Point	Vout - Vin	_	65	_	mV			
I _{ROCP}	Reverse Current Limit	V _{OUT} - V _{IN} = 150mV	_	0.32	_	Α			
t _{TRIG}	Time from Reverse-Voltage Condition to MOSFET Turn Off	V _{IN} = 5V	2	7.5	20	ms			
Fault Flag									
V_{OL}	FAULT Output Low Voltage	I _{FAULT} = 1mA	_	_	180	mV			
I _{FOH}	FAULT Off Current	V _{FAULT} = 5.5V	_	_	1	μA			
t _{BLANK}	FAULT Blanking Time	Assertion or deassertion due to overcurrent and overtemperature condition	2	7.5	20	ms			
Thermal Sh	Thermal Shutdown								
T _{SHDN}	Thermal Shutdown Threshold	Enabled	_	+150	_	°C			
T _{HYS}	Thermal Shutdown Hysteresis	_	_	+40	_	°C			

Typical Performance Characteristics

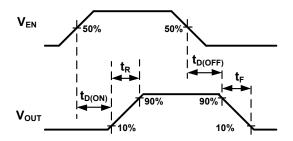
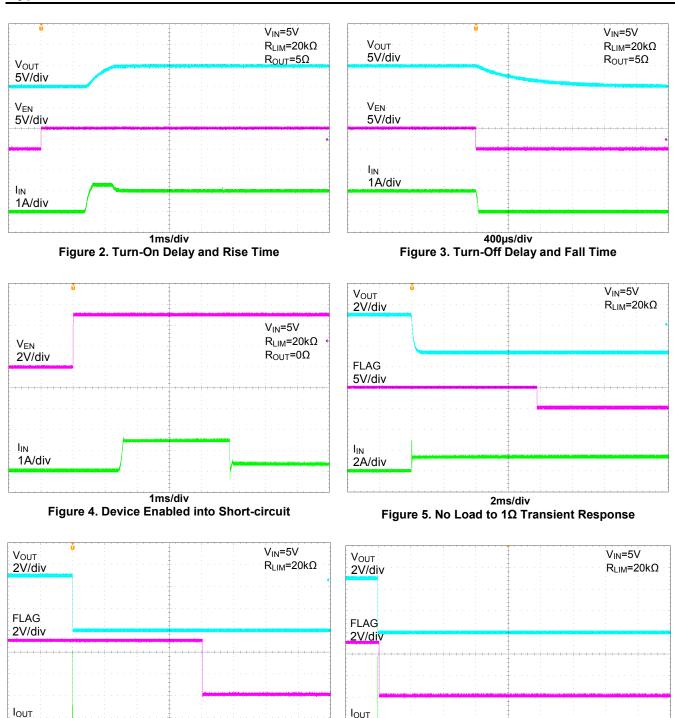


Figure 1. Voltage Waveform



Typical Performance Characteristics (continued)



2ms/div
Figure 6. Short-Circuit Current Limit Response

200ms/div Figure 7. Extended Short-Circuit into Thermal Cycles

2A/div

2A/div



Typical Performance Characteristics (continued)

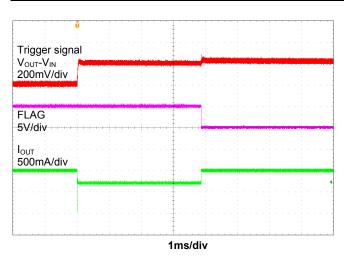


Figure 8. Reverse Current Limit Response

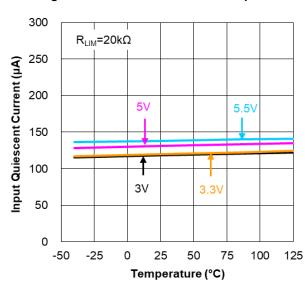


Figure 10. Input Quiescent Current vs. Temperature

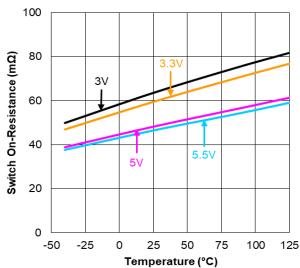


Figure 12. Switch On-Resistance vs. Temperature

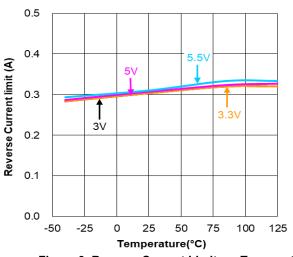


Figure 9. Reverse Current Limit vs. Temperature

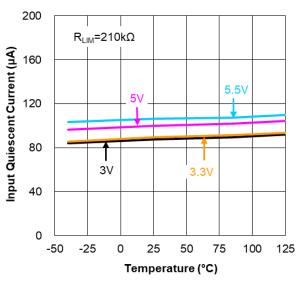


Figure 11. Input Quiescent Current vs. Temperature

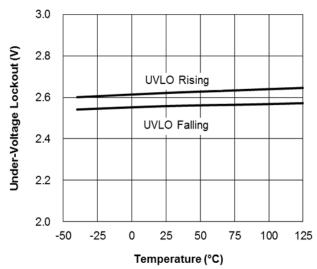


Figure 13. Under-Voltage Lock Out vs. Temperature



Application Information

The AP22653Q is an automotive-compliant high-side power switch optimized for ECU supply rail power distribution, current-limiting, and Universal Serial Bus (USB) power rails that require protection functions in automotive systems. The power switches are equipped with a driver that controls the gate voltage and incorporates slew-rate limitation. This, along with its various protection features and special functions, makes these power switches ideal for hot-swap or hot-plug applications.

Protection Features

Undervoltage Lockout (UVLO)

Whenever the input voltage falls below UVLO threshold (~2.5V), the power switch is turned off. This facilitates the design of hot-insertion systems where it is not possible to turn off the power switch before input power is removed.

Overcurrent and Short-Circuit Protection

An internal sensing FET is employed to check for overcurrent conditions. Unlike current-sense resistors, sense FETs do not increase the series resistance of the current path. When an overcurrent condition is detected, the AP22653Q maintains a constant output current and reduces the output voltage accordingly. Complete shutdown occurs only if the fault stays long enough to activate thermal limiting.

The different overload conditions and the corresponding response of the AP22653Q are outlined below:

NO.	Conditions	Explanation	Behavior of the AP22653Q
1	Short-circuit condition at start-up	Output is shorted before input voltage is applied or before the part is enabled.	The IC senses the short circuit and immediately clamps output current to a certain safe level namely I _{SHORT} .
2	Short-circuit or overcurrent condition	Short-Circuit or Overload condition that occurs when the part is enabled.	At the instance the overload occurs, higher current may flow for a very short period of time before the current limit function can react. After the current limit function has tripped (reached the overcurrent trip threshold), the device switches into current limiting mode and the current is clamped at I _{SHORT} /I _{LIMIT} .
3	Gradual increase from nominal operating current to I _{LIMIT}	Load increases gradually until the current-limit threshold. (I _{TRIG})	The current rises until I_{LIMIT} or thermal limit. Once the threshold has been reached, the device switches into its current limiting mode and is set at I_{LIMIT} .

Current-Limit Threshold Programming

The current-limit threshold can be programmed using an external resistor. The current-limit threshold is proportional to the current sourced out of I_{LIM} .

The recommended 1% resistor range for R_{LIM} is $15k\Omega \le R_{LIM} \le 210k\Omega$. Figure 14 includes current-limit tolerance due to variations caused by temperature and process. This graph does not include the external resistor tolerance. The traces routing the RLIM resistor to the AP22653Q should be as short as possible to reduce parasitic effects on the current-limit accuracy.

To design below a maximum current-limit threshold, find the intersection of R_{LIM} and the maximum desired load current on the $I_{OS(max)}$ (I_{LIM}) curve and choose a value of R_{LIM} above this value. Programming the current limit below a maximum threshold is important to avoid current limiting upstream power supplies causing the input voltage bus to drop. The resulting minimum current-limit threshold is the intersection of the selected value of R_{LIM} and the $I_{OS(min)}$ (I_{LIM}) curve.

Best Fit Current-Limit Threshold Equations (ILIMIT):

$$I_{\text{LIMIT_Min}} = 28955 / R[k\Omega]^{1.075} \qquad I_{\text{LIMIT_Typ}} = 30321 / R[k\Omega]^{1.055} \qquad I_{\text{LIMIT_Max}} = 31033 / R[k\Omega]^{1.031}$$



Application Information (continued)

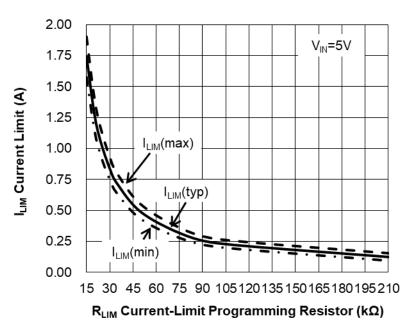


Figure 14. Current-Limit Threshold vs. R_{LIM}

Thermal Protection

Thermal protection prevents the IC from damage when the die temperature exceeds safe margins. This mainly occurs when heavy-overload or short-circuit faults are present for extended periods of time. The AP22653Q implements a thermal sensing to monitor the operating junction temperature of the power distribution switch. Once the die temperature rises to approximately +150°C, the thermal protection feature activates as follows: The internal thermal sense circuitry turns the power switch off and the FAULT output is asserted, thus preventing the power switch from damage. Hysteresis in the thermal sense circuit allows the device to cool down by approximately +40°C before the output is turned back on. This built-in thermal hysteresis feature is an excellent feature, as it avoids undesirable oscillations of the thermal protection circuit.

Reverse-Current and Reverse-Voltage Protection

The USB specification does not allow an output device to source current back into the USB port. In a normal MOSFET switch, current will flow in reverse direction (from the output side to the input side) when the output side voltage is higher than the input side. A reverse-current limit (ROCP) feature is implemented in the AP22653Q to limit such back currents. The ROCP circuit is activated when the output voltage is higher than the input voltage. After the reverse current circuit has tripped (reached the reverse current trip threshold), the current is clamped at this IROCP level.

In addition to ROCP, reverse overvoltage protection (ROVP) is also implemented. The ROVP circuit is activated by the reverse voltage comparator trip point; i.e., the difference between the output voltage and the input voltage.

For the AP22653Q, once ROVP is activated, FAULT assertion occurs at a deglitch time of 6ms. Recovery from ROVP is automatic when the fault is removed. FAULT deassertion deglitch time is same as the deassertion time.

Special Functions

Discharge Function

When enable is deasserted, or when the input voltage is under UVLO level, the discharge function is active. The output capacitor is discharged through an internal NMOS that has a discharge resistance of 600Ω . Hence, the output voltage drops down to zero. The time taken for discharge is dependent on the RC time constant of the resistance and the output capacitor.



Application Information (continued)

FAULT Response

The FAULT open-drain output goes active low for any of following faults: overcurrent, OUT pin short-circuit, reverse-voltage condition, or thermal shutdown. The time from when a fault condition is encountered to when the FAULT output goes low is 7.5ms (Typ). The FAULT output remains low until overcurrent, OUT pin short-circuit, and overtemperature conditions are removed. Connecting a heavy capacitive load to the output of the device can cause a momentary overcurrent condition, which does not trigger the FAULT due to the 7.5ms deglitch timeout. This 7.5ms timeout is also applicable for overcurrent recovery and overtemperature recovery. The AP22653Q is designed to eliminate erroneous overcurrent reporting without the need for external components, such as an RC delay network.

For the AP22653Q when the reverse voltage condition is triggered, FAULT output goes low after 7.5ms (Typ). This 7.5ms (Typ) timeout is also applicable for the recovery from reverse voltage fault. The flag current is always higher than current-limit threshold to ensure maximum loading consuming.

When the ILIM pin is shorted to GND, current-limit threshold and short-circuit current limit will be clamped at typically 100mA. When the ILIM pin is shorted to GND, the AP22653Q FAULT pin will assert during current-limiting and short-circuit conditions.

Power Supply Considerations

A $0.01\mu\text{F}$ to $0.1\mu\text{F}$ X7R or X5R ceramic bypass capacitor between IN and GND, close to the device, is recommended. This limits the input voltage drop during line transients. Placing a high-value electrolytic capacitor on the input ($10\mu\text{F}$ minimum) and output pin ($120\mu\text{F}$) is recommended when the output load is heavy. This precaution also reduces power-supply transients that may cause ringing on the input. Additionally, bypassing the device output with a $0.1\mu\text{F}$ to $4.7\mu\text{F}$ ceramic capacitor improves the immunity of the device to short-circuit transients. This capacitor also prevents output from going negative during turn-off due to parasitic inductance.

Power Dissipation and Junction Temperature

The low on-resistance of the internal MOSFET allows the small surface-mount packages to pass large currents. Using the maximum operating ambient temperature (T_A) and R_{DS(ON)}, the power dissipation can be calculated by:

$$P_D = R_{DS(ON)} \times I^2$$

Finally, calculate the junction temperature:

$$T_J = P_D \times \Theta_{JA} + T_A$$

Where:

 T_A = Ambient temperature °C θ_{JA} = Thermal resistance P_D = Total power dissipation

Generic Hot-Plug Applications

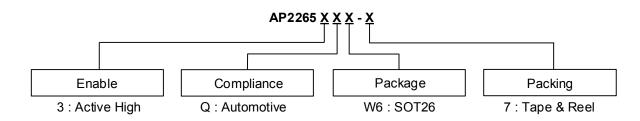
In many applications it may be necessary to remove modules or PC boards while the main unit is still operating. These are considered hot-plug applications. Such implementations require the control of current surges seen by the main power supply and the card being inserted. The most effective way to control these surges is to limit and slowly ramp the current and voltage being applied to the card, similar to the way in which a power supply normally turns on. Due to the controlled rise and fall times of the AP22653Q, this device can be used to provide a softer start-up to devices being hot-plugged into a powered system. The UVLO feature of the AP22653Q also ensures that the switch is off after the card has been removed, and that the switch is off during the next insertion.

Generic Hot-Plug Applications

By placing the AP22653Q between the V_{CC} input and the rest of the circuitry, the input power reaches these devices first after insertion. The typical rise time of the switch is approximately 1ms, providing a slow voltage ramp at the output of the device. This implementation controls system surge current and provides a hot-plugging mechanism for any device.



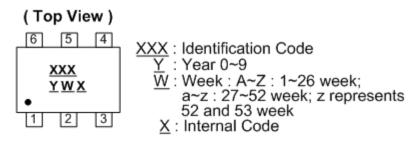
Ordering Information



		Enable	Output Foult	Dookogo		Moisture	7" Tape	and Reel
Part Number	Compliance	Active	Output Fault Condition	Package Code	Packaging	Sensitivity	Quantity	Part Number Suffix
AP22653QW6-7	Automotive	High	Output Current Limits	W6	SOT26 (Type A1)	MSL 1	3000 /Tape & Reel	-7

Marking Information

SOT26 (Type A1)



Туре	Part Number	Package	Identification Code
Grade1	AP22653QW6-7	SOT26 (Type A1)	FKQ

Mechanical Data

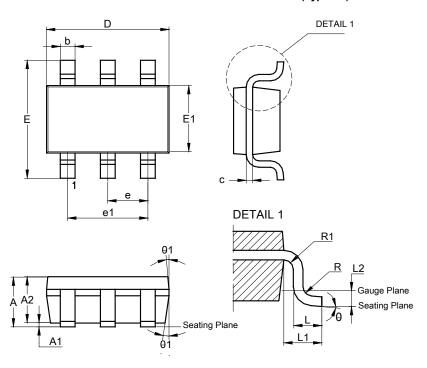
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26 (Type A1)

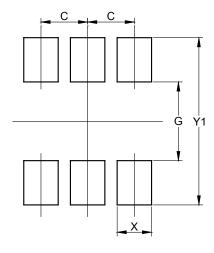


SOT26 (Type A1)						
Dim	Min	Min Max Typ				
Α	-	1.45				
A1	0.00	0.15				
A2	0.90	1.30	1.15			
b	0.30	0.50				
С	0.08	0.22				
D		2.90 B	SC			
Е		2.80 B	SC			
E1		1.60 B	SC			
е		0.95 B	SC			
e1		1.90 B	SC			
L	0.30	0.60	0.45			
L1		0.60 R	EF			
L2		0.25 B	SC			
R	0.10					
R1	0.10	0.25				
θ	0°	8°	4°			
θ1	5°	15°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT26 (Type A1)



Dimensions	Value
Dillicitations	(in mm)
С	0.950
G	1.600
X	0.700
Y	0.900
Y1	3.400



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